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RGPR30NS40HR

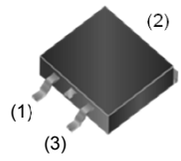
400V 30A Ignition IGBT

Datasheet

BV_{CES}	400±30V
I_C	30A
$V_{CE(sat)}$ (Typ.)	1.6V
E_{AS}	300mJ

●Outline

LPDS (TO-263S) / TO-262





●Features

1) Low Collector - Emitter Saturation Voltage

2) High Self-Clamped Inductive Switching Energy

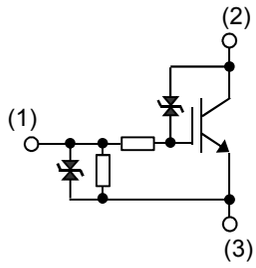
3) Built in Gate-Emitter Protection Diode

4) Built in Gate-Emitter Resistance

5) Qualified to AEC-Q101

6) Pb - free Lead Plating ; RoHS Compliant

●Inner Circuit



(1) Gate
(2) Collector
(3) Emitter

●Packaging Specifications

Type	Packaging	Taping / Tube
	Reel Size (mm)	330 / -
	Tape Width (mm)	24 / -
	Basic Ordering Unit (pcs)	1,000 / 1,000
	Packing Code	TL / C9
	Marking	RGPR30NS40

●Applications

Ignition Coil Driver Circuits

Solenoid Driver Circuits

●Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CES}	430	V
Emitter-Collector Voltage (V_{GE} = 0V)		V_{EC}	25	V
Gate - Emitter Voltage		V_{GES}	±10	V
Collector Current		I_C	30	A
Avalanche Energy (Single Pulse)	T_j = 25°C	E_{AS}	300	mJ
	T_j = 150°C	E_{AS} *2	180	mJ
Power Dissipation		P_D	125	W
Operating Junction Temperature		T_j	−40 to +175	°C
Storage Temperature		T_{stg}	−55 to +175	°C

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●Thermal Resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	1.20	°C/W

●Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector - Emitter Breakdown Voltage	BV_{CES}	I_C = 2mA, V_{GE} = 0V				
		T_j = 25°C	370	400	430	V
		T_j = –40 to 175°C*2	365	-	435	V
Emitter - Collector Breakdown Voltage	BV_{EC}	I_C = –10mA, V_{GE} = 0V	25	35	-	V
Gate - Emitter Breakdown Voltage	BV_{GES}	I_G = ±5mA, V_{CE} = 0V	±12	-	±17	V
Collector Cut - off Current	I_{CES}	V_{CE} = 250V, V_{GE} = 0V				
		T_j = 25°C	-	-	7	μA
		T_j = 150°C*2	-	-	100	μA
Gate - Emitter Leakage Current	I_{GES}	V_{GE} = ±10V, V_{CE} = 0V	±0.4	±0.6	±1.2	mA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	V_{CE} = 5V, I_C = 12mA				
		T_j = 25°C	1.3	1.7	2.1	V
		T_j = 150°C*2	-	1.3	-	V
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 12A, V_{GE} = 5V				
		T_j = 25°C	-	1.60	2.00	V
		T_j = 150°C	-	1.80	-	V
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 5A, V_{GE} = 4.5V				
		T_j = 25°C	-	1.17	1.50	V
		T_j = 150°C	-	1.19	-	V

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●**Electrical Characteristics** (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 12A, V_{GE} = 4V				
		T_j = 25°C	-	1.70	2.10	V
		T_j = 150°C	-	1.90	-	V
Input Capacitance	C_{ies}	V_{CE} = 10V	-	1330	-	pF
Output Capacitance	C_{oes}	V_{GE} = 0V	-	220	-	pF
Reverse Transfer Capacitance	C_{res}	f = 1MHz	-	71	-	pF
Total Gate Charge	Q_g	V_{CE} = 12V, I_C = 10A, V_{GE} = 5V	-	22	-	nC
Turn - on Delay Time[*1,*2]	$t_{d(on)}$	I_C = 8A, V_{CC} = 300V, V_{GE} = 5V, R_G = 100Ω, L=5mH, T_j=25°C	0.11	0.19	0.50	µs
Rise Time[*1,*2]	t_r		0.10	0.18	0.50	µs
Turn - off Delay Time[*1,*2]	$t_{d(off)}$		0.9	1.4	4.0	µs
Fall Time[*1,*2]	t_f		0.8	1.8	5.5	µs
Turn - on Delay Time[*1]	$t_{d(on)}$	I_C = 8A, V_{CC} = 300V, V_{GE} = 5V, R_G = 100Ω, L=5mH, T_j=150°C	-	0.18	-	µs
Rise Time[*1]	t_r		-	0.21	-	µs
Turn - off Delay Time[*1]	$t_{d(off)}$		-	1.7	-	µs
Fall Time[*1]	t_f		-	3.0	-	µs
Avalanche Energy (Single Pulse)	E_{AS}	L = 5mH, V_{GE} = 5V, V_{CC} = 30V, R_G = 1kΩ,				
		T_j = 25°C	300	-	-	mJ
		T_j = 150°C[*2]	180	-	-	mJ
Gate Series Resistance	R_G		70	100	130	Ω
Gate - Emitter Resistance	R_{GE}		8	16	24	kΩ

*1) Assurance items according to our measurement definition (Fig.18)

*2) Design assurance items

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●Electrical Characteristic Curves

Fig.1 Typical Output Characteristics

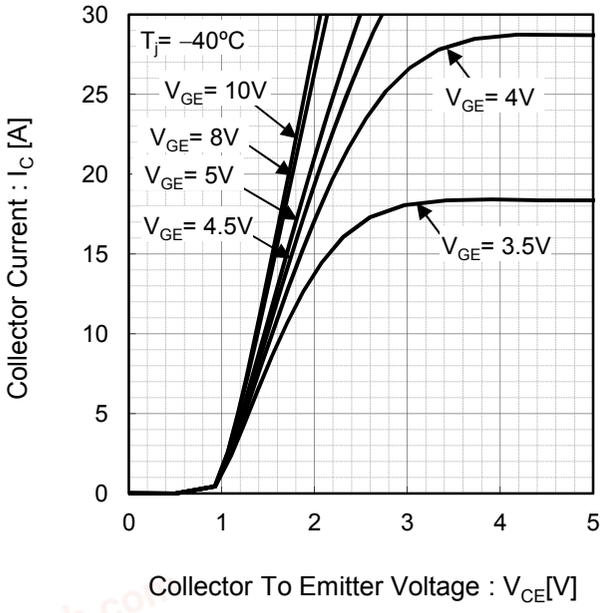


Fig.2 Typical Output Characteristics

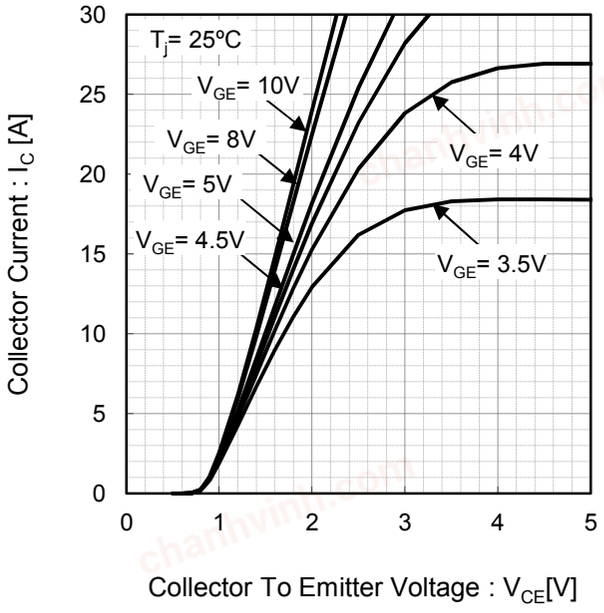


Fig.3 Typical Output Characteristics

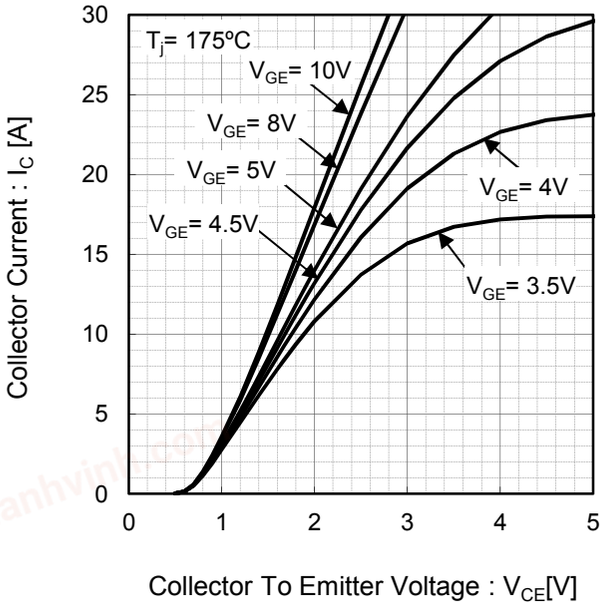
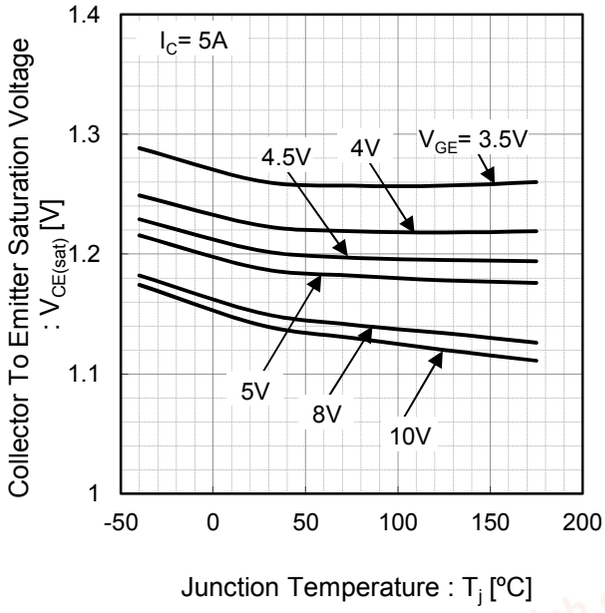


Fig.4 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



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●Electrical Characteristic Curves

Fig.5 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

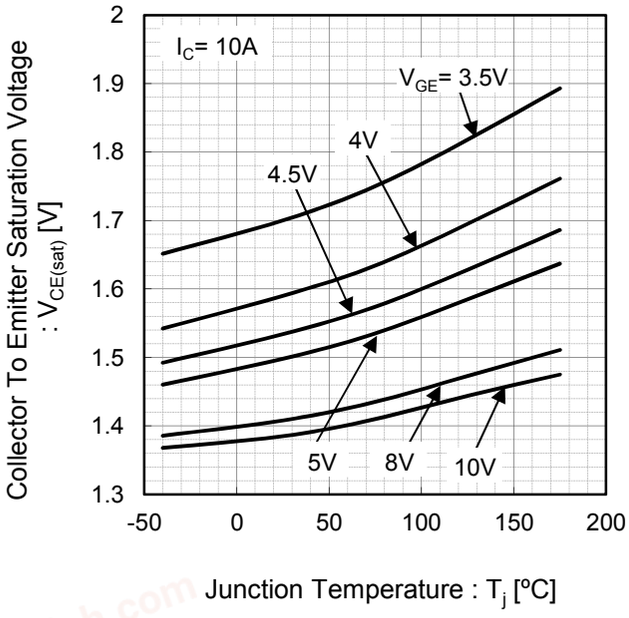


Fig.6 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

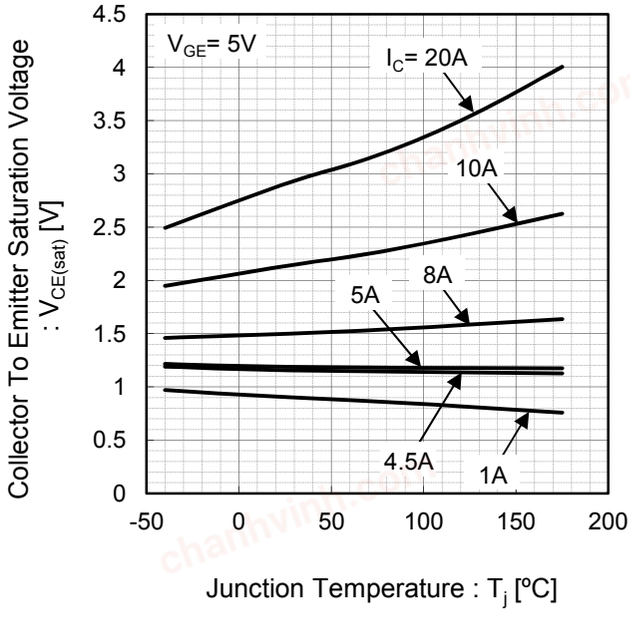


Fig.7 Typical Transfer Characteristics

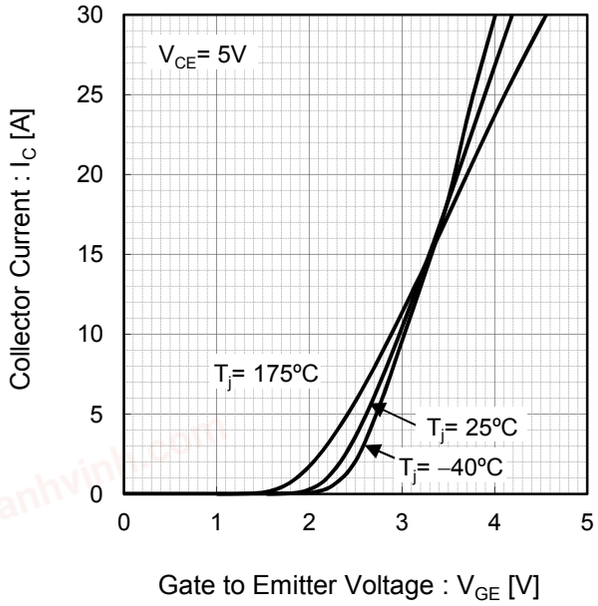
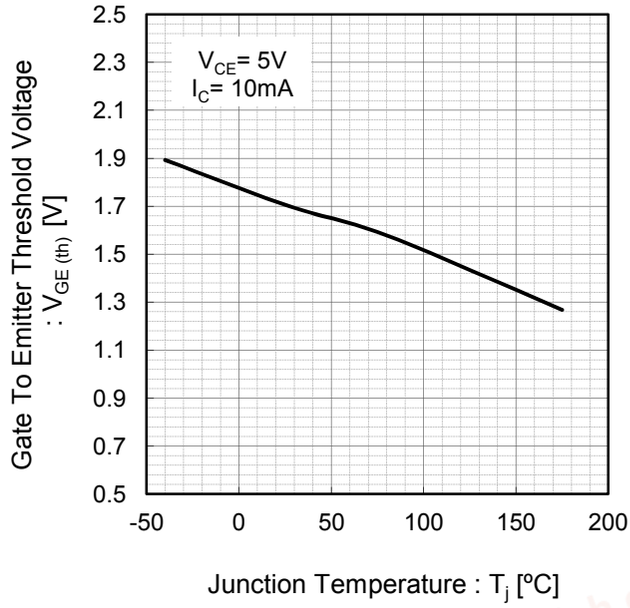


Fig.8 Typical Gate To Emitter Threshold Voltage vs. Junction Temperature



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●Electrical Characteristic Curves

Fig.9 Typical Leakage Current vs. Junction Temperature

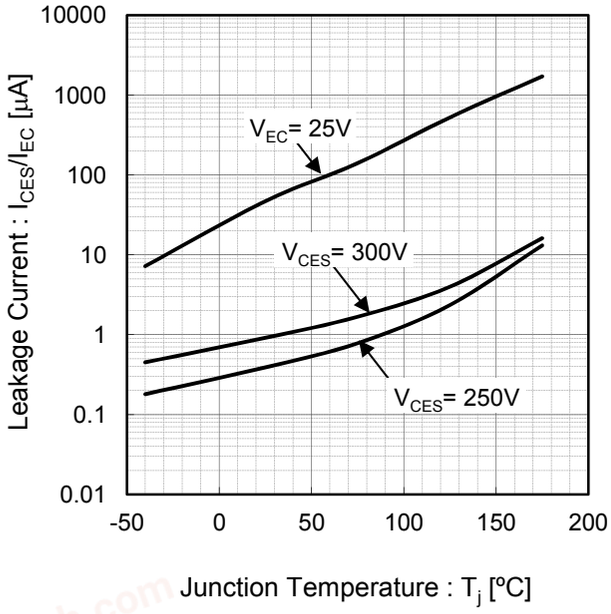


Fig.10 Typical Collector To Emitter Breakdown Voltage vs. Junction Temperature

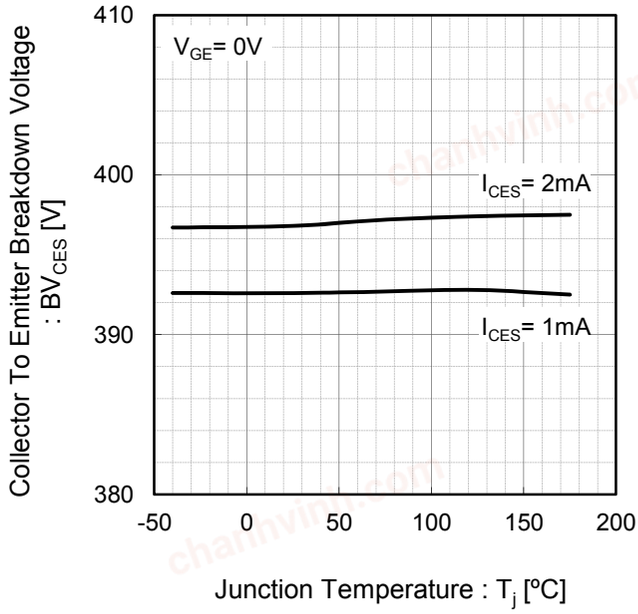


Fig.11 Typical Self Clamped Inductive Switching Current vs. Inductance

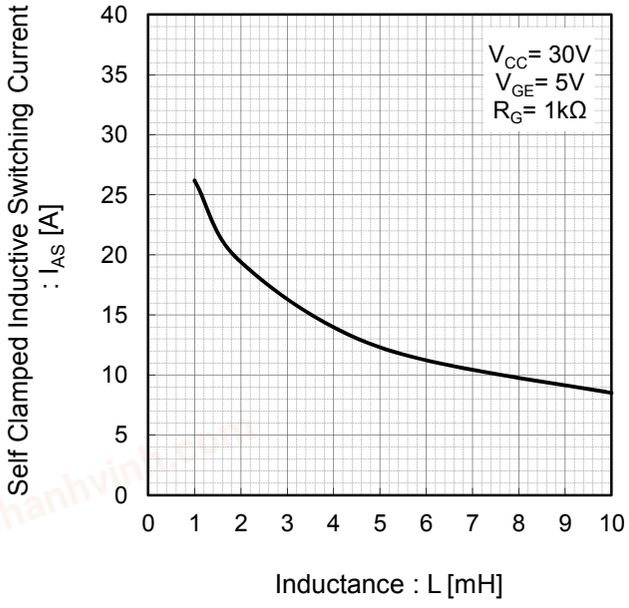
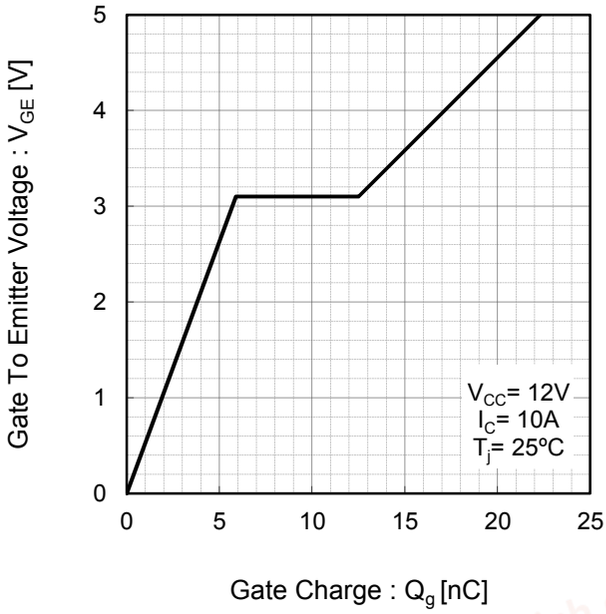


Fig.12 Typical Gate Charge



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●Electrical Characteristic Curves

Fig.13 Typical Capacitance vs. Collector To Emitter Voltage

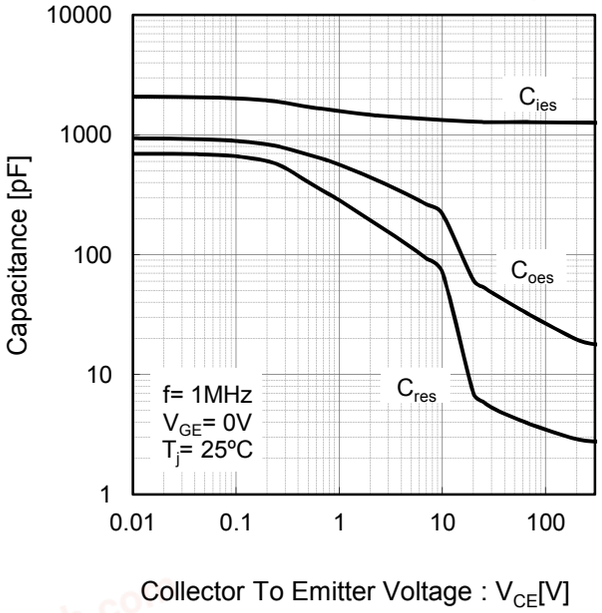


Fig.14 Typical Switching Time vs. Junction Temperature

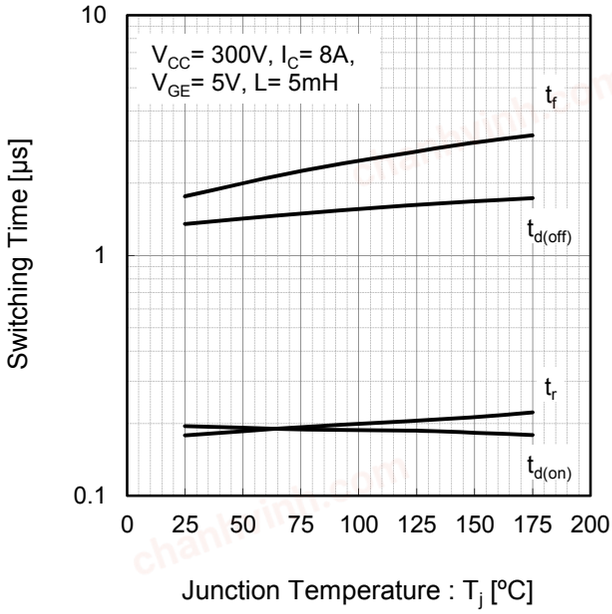
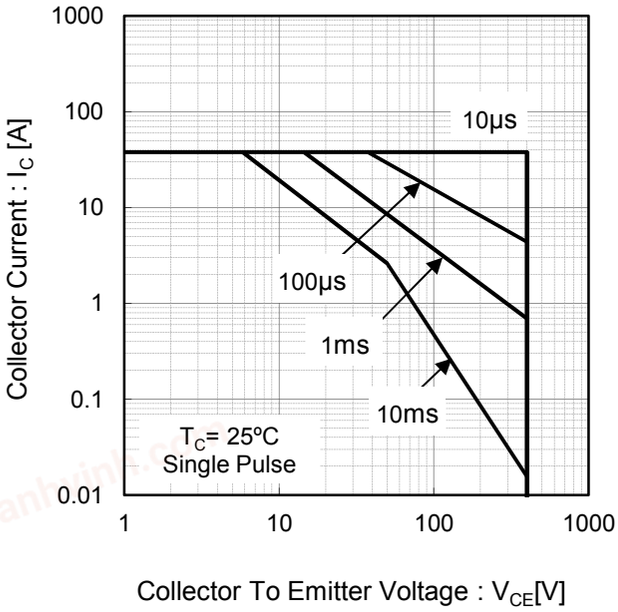


Fig.15 Forward Bias Safe Operating Area

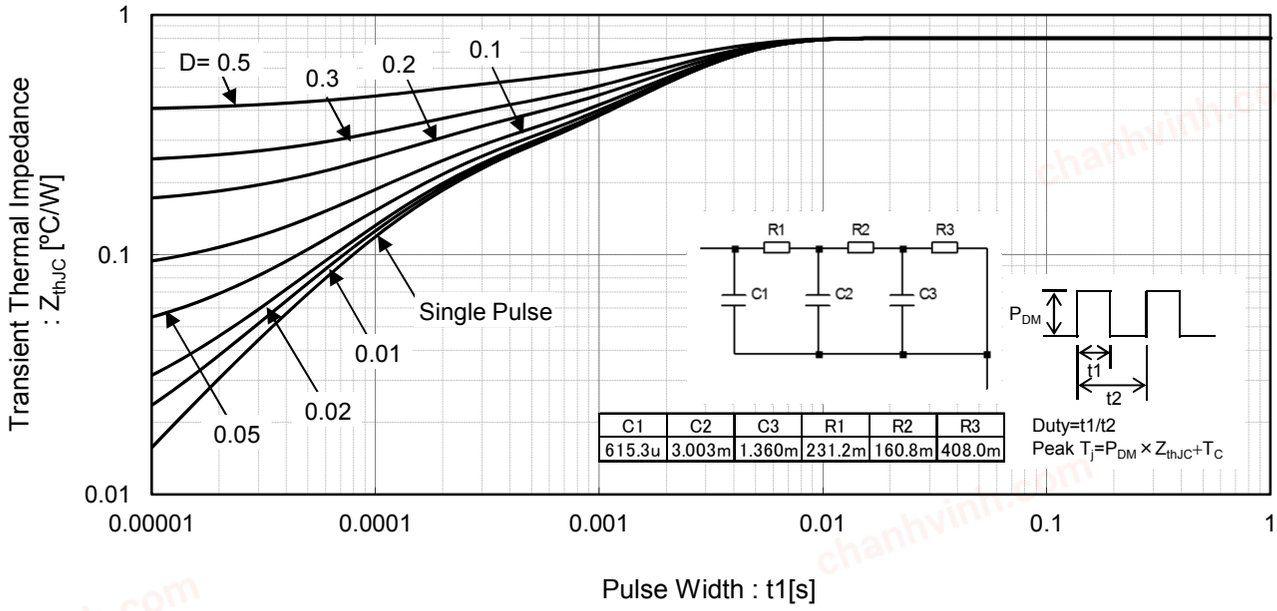


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●Electrical Characteristic Curves

Fig.16 Transient Thermal Impedance



C1	C2	C3	R1	R2	R3
615.3u	3.003m	1.360m	231.2m	160.8m	408.0m

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●Inductive Load Switching Circuit and Waveform

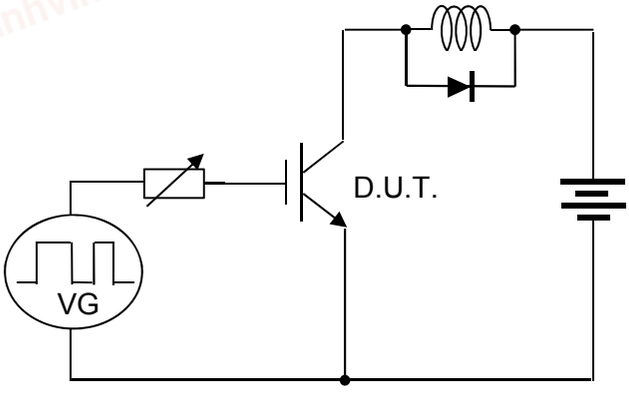


Fig.17 Inductive Load Switching Circuit

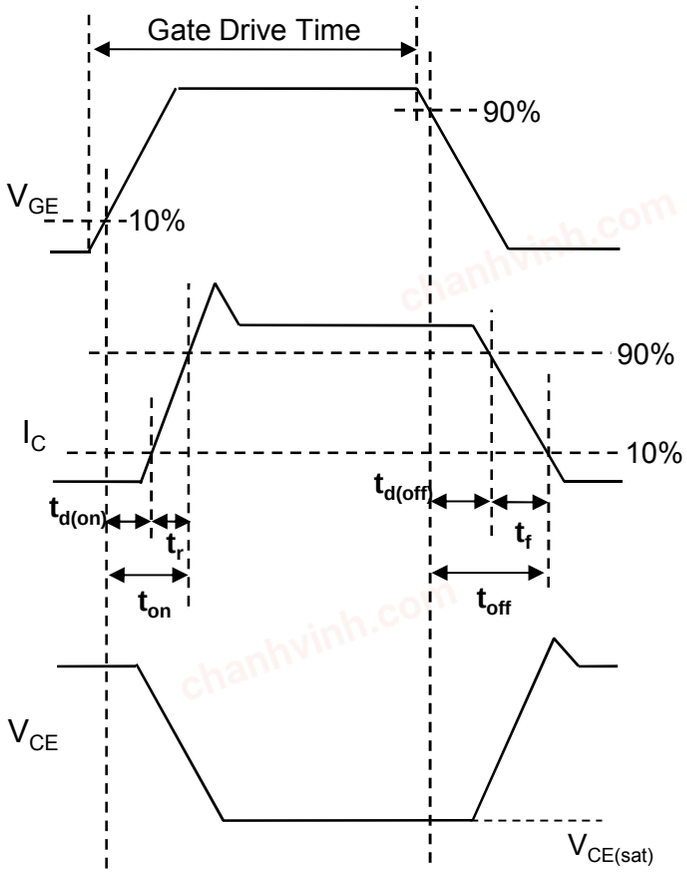


Fig.18 Inductive Load Switching Waveform

●Self Clamped Inductive Switching Circuit and Waveform

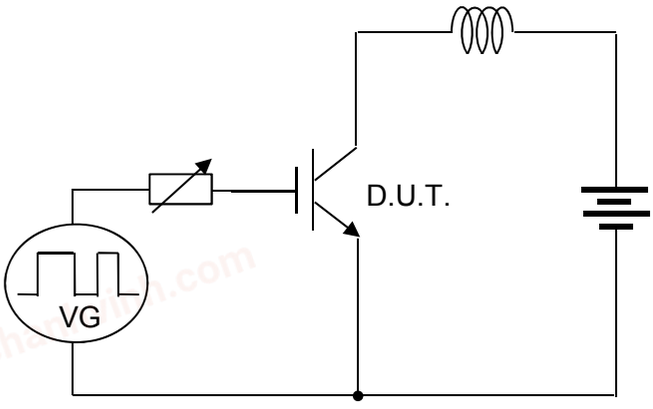


Fig.19 Self Clamped Inductive Switching Ciruit

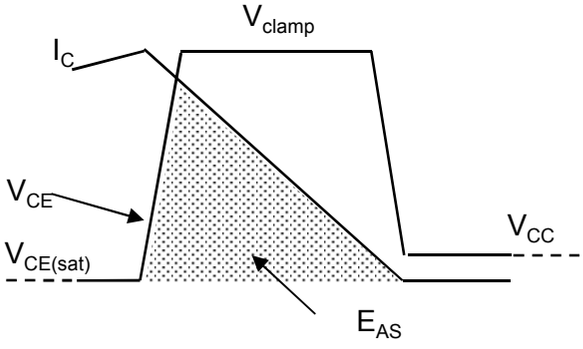


Fig.20 Self Clamped Inductive Switching Waveform

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